TOSHIBA Photocoupler GaAs IRed & Photo-Thyristor

TLP741J

Office Machine
Household Use Equipment
Solid State Relay
Switching Power Supply

The TOSHIBA TLP741J consists of a photo–thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

• Peak off-state voltage: 600 V (min.)

• Trigger LED current: 10 mA (max.)

• On-state current: 150 mA (max.)

• UL recognized: UL1577, file no. E67349

• BSI approved: BS EN60065: 1994

Certificate no. 6617 BS EN60950: 1992 Certificate no. 7366

Isolation voltage: 4000 V_{rms} (min.)

• Option (D4) type

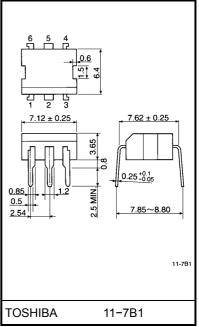
VDE approved: DIN VDE0884 / 08,87 Certificate no. 65640

Maximum operating insulation voltage: $630~\mathrm{VPK}$ Highest permissible over voltage: $6000~\mathrm{VPK}$

(Note) When a VDE0884 approved type is needed, please designate the "option (D4)"

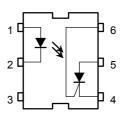
| | | 7.62 mm pich | 10.16 mm pich | | | |
|---|-----------------------|---------------|---------------|--|--|--|
| | | standard type | (LF2) type | | | |
| • | Creepage distance: | 7.0 mm (min.) | 8.0 mm (min.) | | | |
| | Clearance: | 7.0 mm (min.) | 8.0 mm (min.) | | | |
| | Insulation thickness: | 0.5 mm (min.) | 0.5 mm (min.) | | | |

Unit in mm



Weight: 0.35 g

Pin Configuration (top view)



1 : ANODE

2: CATHODE

3 : N.C.

4 : CATHODE

5: ANODE

6 : GATE

Maximum Ratings (Ta = 25°C)

| | Characteristic | Symbol | Rating | Unit | |
|----------|---|----------------------|---------|------------------|--|
| | Forward current | l _F | 60 | mA | |
| | Forward current derating (Ta ≥ 39°C) | ΔI _F / °C | -0.7 | mA / °C | |
| | Peak forward current (100 µs pulse, 100 pps) | I _{FP} | 1 | А | |
| LED | Power dissipation | P _D | 100 | mW | |
| | Power dissipation derating (Ta ≥ 25°C) | ΔP _D / °C | -1.0 | mW / °C | |
| | Reverse voltage | V _R | 5 | V | |
| | Junction temperature | Tj | 125 | °C | |
| | Peak forward voltage (R_{GK} = 27 k Ω) | V_{DRM} | 600 | V | |
| | Peak reverse voltage (R _{GK} = 27 kΩ) | V _{RRM} | 600 | V | |
| | On–state current | I _{T(RMS)} | 150 | mA | |
| | On–state current derating (Ta ≥ 25°C) | ΔI _T / °C | -2.0 | mA / °C | |
| Detector | Peak on-state current (100µs pulse, 120 pps) | I _{TP} | 3 | А | |
| Dete | Peak one cycle surge current | I _{TSM} | 2 | Α | |
| | Peak reverse gate voltage | V_{GM} | 5 | V | |
| | Power dissipation | P_{D} | 150 | mW | |
| | Power dissipation derating (Ta ≥ 25°C) | ΔP _D / °C | -2.0 | mW / °C | |
| | Junction temperature | Tj | 100 | °C | |
| Storage | e temperature range | T _{stg} | -55~125 | °C | |
| Operat | ing temperature range | T _{opr} | -55~100 | °C | |
| Lead s | oldering temperature (10 s) | T _{sol} | 260 | °C | |
| Total p | ackage power dissipation | PT | 250 | mW | |
| Total p | ackage power dissipation derating (Ta ≥ 25°C) | ΔP _T / °C | -3.3 | mW / °C | |
| Isolatio | n voltage (AC, 1 min., R.H.≤ 60%) | BVS | 4000 | V _{rms} | |

Recommended Operating Conditions

| Characteristic | Symbol | Min. | Тур. | Max. | Unit |
|----------------------------|------------------|------|------|------|-----------------|
| Supply voltage | V _{AC} | _ | _ | 240 | V _{ac} |
| Forward current | I _F | 15 | 20 | 25 | mA |
| Operating temperature | T _{opr} | -25 | _ | 85 | °C |
| Gate to cathode resistance | R _{GK} | _ | 10 | 27 | kΩ |
| Gate to cathode capacity | C _{GK} | _ | 0.01 | 0.1 | μF |

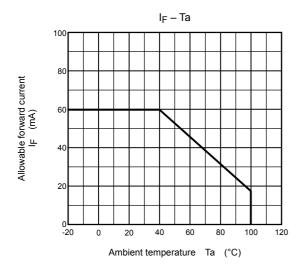
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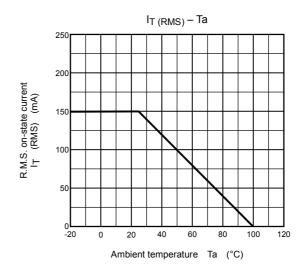
Individual Electrical Characteristics (Ta = 25°C)

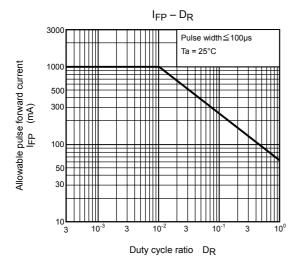
| Characteristic | | Symbol | Test Condition | | Min. | Тур. | Max. | Unit |
|----------------|----------------------------|------------------|--|---------------|------|------|------|------|
| | Forward voltage | V _F | I _F = 10 mA | | 1.0 | 1.15 | 1.3 | V |
| E | Reverse current | I _R | V _R = 5 V | | - | _ | 10 | μΑ |
| | Capacitance | C _T | V = 0, f = 1 MHz | | _ | 30 | _ | pF |
| | Off-state current | l== | V _{AK} = 600 V R _{GK} = 27 kΩ | Ta = 25°C | _ | 10 | 5000 | nA |
| | | IDRM | | Ta = 85°C | _ | 1 | 150 | μA |
| | Reverse carrent | I _{RRM} | V _{KA} = 600 V R _{GK} = 27 kΩ | Ta = 25°C | _ | 10 | 5000 | nA |
| j. | | | | Ta = 85°C | _ | 1 | 150 | μA |
| Detector | On-state voltage | V _{TM} | I _{TM} = 100 mA | | _ | 0.9 | 1.3 | V |
| ۵ | Holding current | lн | R _{GK} = 27 kΩ | | _ | 0.2 | _ | mA |
| | Off–state dv / dt | dv / dt | V _{AK} = 420 V, R _{GK} = 27 kΩ | | _ | 10 | _ | V/µs |
| | Capacitance C _j | 0 | V = 0 f = 4 MH= | Anode to gate | _ | 20 | _ | 25 |
| | | V = 0, f = 1 MHz | Gate to cathode | _ | 350 | _ | pF | |

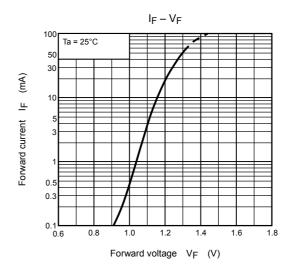
Coupled Characteristics (Ta = 25°C)

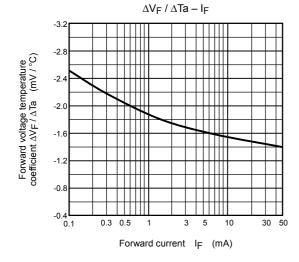
| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit | |
|-------------------------------|-----------------|---|--------------------|------------------|------|------------------|--|
| Trigger LED current | I _{FT} | V_{AK} = 6 V, R_{GK} = 27 k Ω | _ | 5 | 10 | mA | |
| Turn-on time | t _{ON} | $I_F = 30 \text{ mA}, V_{AA} = 50 \text{ V}$ $R_{GK} = 27 \text{ k}\Omega$ | _ | 10 | _ | μs | |
| Coupled dv / dt | dv / dt | $V_S = 500 \text{ V}, R_{GK} = 27 \text{ k}\Omega$ | 500 | - | _ | V / µs | |
| Capacitance (input to output) | CS | V _S = 0, f = 1 MHz | _ | 0.8 | _ | pF | |
| Isolation resistance | R _S | V _S = 500 V | 1×10 ¹² | 10 ¹⁴ | _ | Ω | |
| | BVS | AC, 1 minute | 4000 | _ | _ | W | |
| Isolation voltage | | AC, 1 second, in oil | _ | 10000 | _ | V _{rms} | |
| | | DC, 1 minute, in oil | _ | 10000 | _ | V _{dc} | |

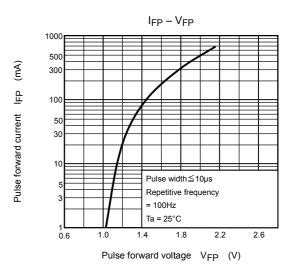


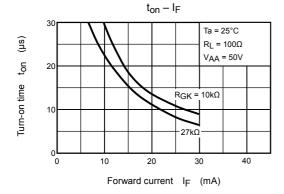


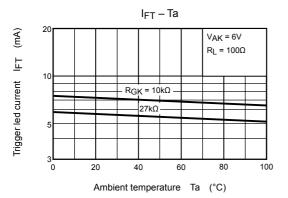


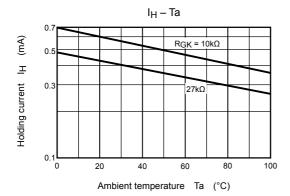


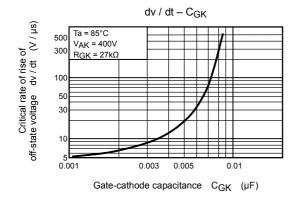


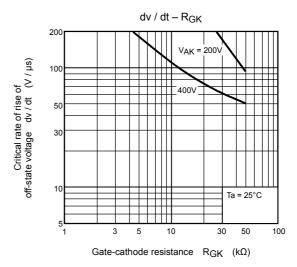


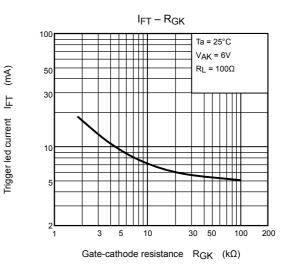


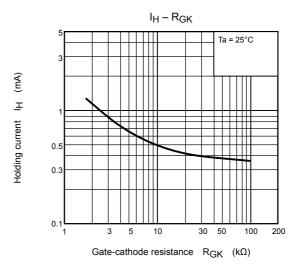












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